Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 https://www.sciencedirect.com/science/article/pii/S0040609009014564

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf